



### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	$2\Omega$ @ $V_{GS} = 10V$	320mA
607	$3\Omega$ @ $V_{GS} = 5V$	260mA

### **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- Power Management Functions

SOT-523





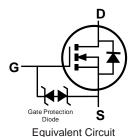
Top View

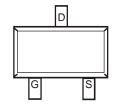
### **Features**

- Low On-Resistance: R<sub>DS(ON)</sub>
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)





Top View Pin Out Configuration

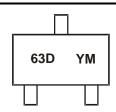
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN63D1LT-7	SOT-523	3000/Tape & Reel
DMN63D1LT-13	SOT-523	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



63D = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2014	2	2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		Е	F		G	Н		I
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6), $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	320 260	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	I <sub>S</sub>	0.5	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	6)	I <sub>DM</sub>	1.2	Α	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_D$	260	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	497	°C/W
Total Power Dissipation (Note 6)	·	P <sub>D</sub>	330	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	389	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

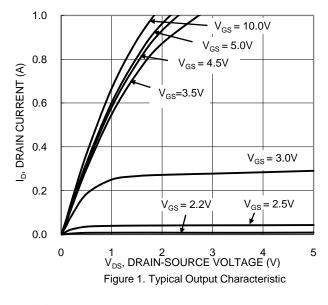
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

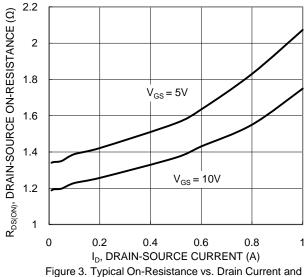
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	D		_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Dialif-Source Off-Nesistance	R <sub>DS(ON)</sub>		_	3.0	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y <sub>fs</sub>	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	$V_{SD}$	_	0.75	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>		30	_	рF	V 05V V 0V
Output Capacitance	Coss		4.2	_	рF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>		2.9	_	рF	1 = 1.01/11 12
Gate Resistance	Rg	_	133	_	Ω	$f = 1MHz$ , $V_{GS} = 0V$ , $V_{DS} = 0V$
Total Gate Charge	$Q_g$		392	_	рC	1/ 45)/ // 40)/
Gate-Source Charge	Qgs	_	157	_	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	$Q_{gd}$	_	92	_	рC	I <sub>D</sub> = 250mA
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.9	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	3.4	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	15.7		ns	$R_G = 25\Omega$ , $I_D = 200mA$
Turn-Off Fall Time	t <sub>F</sub>	_	9.9	_	ns	

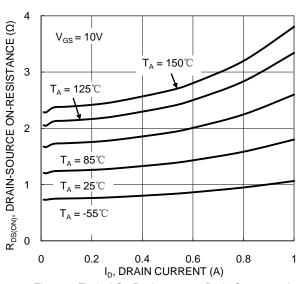
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
    7. Short duration pulse test used to minimize self-heating effect.

  - 8. Guaranteed by design. Not subject to product testing.



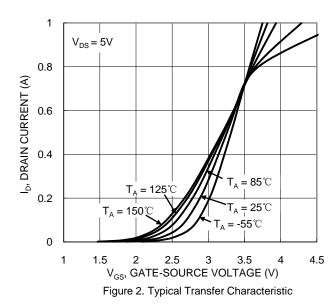






Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature



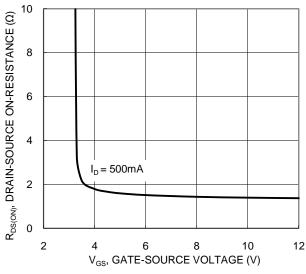


Figure 4. Typical Transfer Characteristic

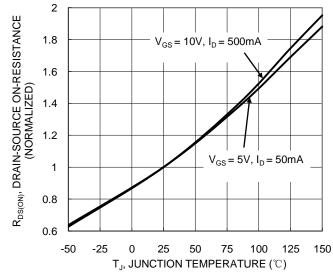


Figure 6. On-Resistance Variation with Junction Temperature



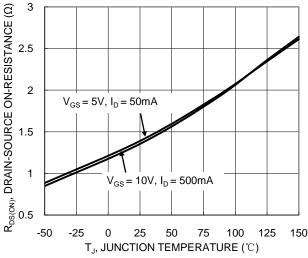
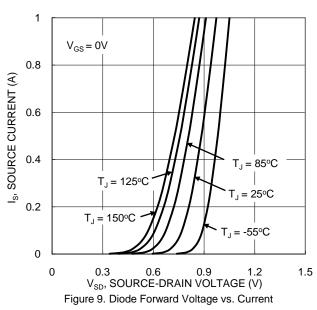
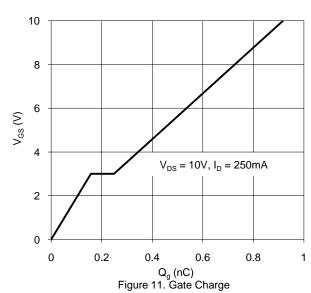


Figure 7. On-Resistance Variation with Junction Temperature





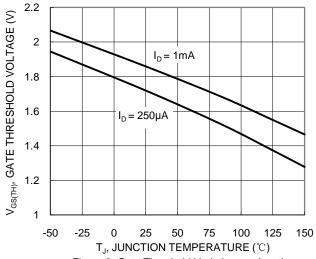


Figure 8. Gate Threshold Variation vs. Junction Temperature

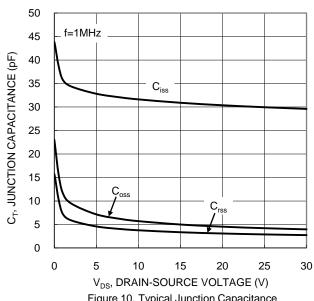
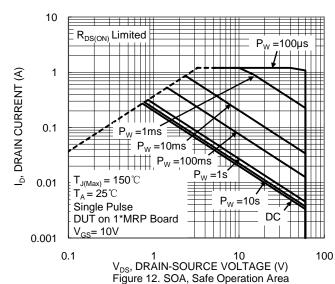
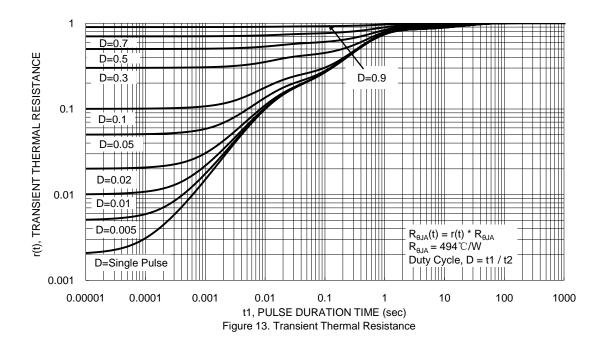


Figure 10. Typical Junction Capacitance



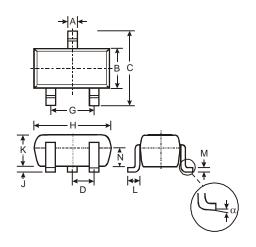




## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

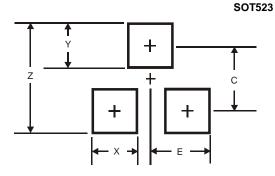
#### **SOT523**



SO1523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
С	1.45	1.75	1.60				
D	_	_	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
K	0.60	0.80	0.75				
L	0.10	0.30	0.22				
M	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	α 0° 8° —						
All Dimensions in mm							

## **Suggested Pad Layout**

 $Please see AP02001 \ at \ http://www.diodes.com/datasheets/ap02001.pdf \ for \ the \ latest \ version.$ 



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7



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